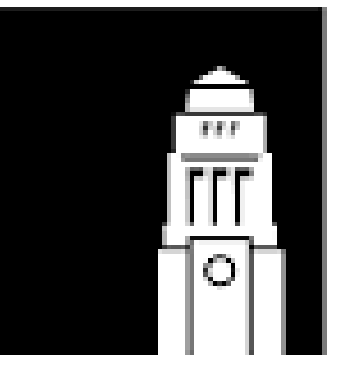


# Low Temperature Annealing of Superconducting Bismuth Nickel Bilayers

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## Abstract

This work shows bismuth nickel bilayers will anneal at room temperature over a period of 2 weeks, increasing the superconducting  $T_C$  of the sample until it has saturated to 3.8 k. During annealing bismuth atoms diffuses across the interface forming a  $\text{NiBi}_3$  alloy which has a similar  $T_C$  of 4.1 k. The activation energy for this annealing is  $(0.86 \pm 0.06)$  eV and it is also observed that heating at temperatures as little as  $50^\circ\text{C}$  for 1 hour is enough to cause a significant increase in the  $T_C$ . This aging process poses a challenge to studying distinct Bi/Ni bilayers as any slight heating will degrade the interface.

## Introduction

- Superconductivity was initially noticed in bismuth growth on a nickel dusting in 1990 after which not much happen until recently [1]
- The recent interest is the potential for unusual superconductivity at the interface. Given the close proximity of superconductivity, ferromagnetism and strong spin orbit coupling there are several proposed origins:
  1. p-wave superconductivity [2]
  2. Non-trivial topology [3]
  3. Spontaneous formation of  $\text{NiBi}_3$  alloy during growth process [4]
- Since bismuth has a low melting point it is important to look at what temperatures and timescales diffusion across the interface is significant. Also if this diffusion forms the superconducting  $\text{NiBi}_3$  alloy
- With  $\text{NiBi}_3$  at the interface it would not exclude some of the other possibilities but it is important to take into consideration this annealing process

## Conclusion

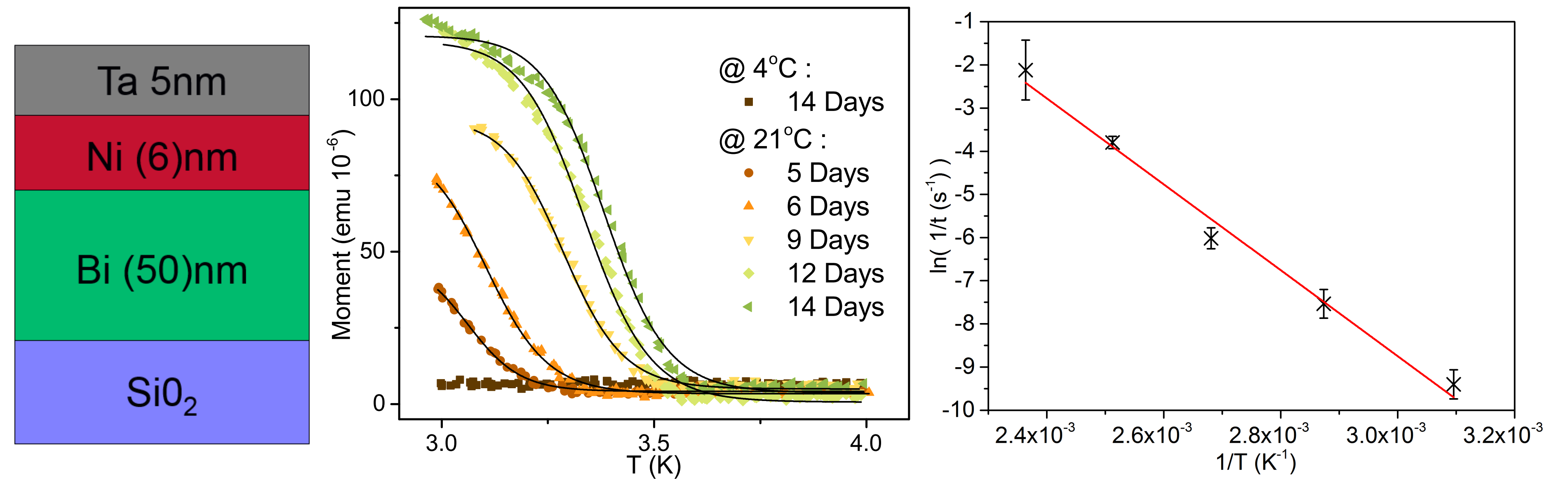
- Bismuth nickel interfaces will anneal at low temperatures increasing the superconducting  $T_C$ , to properly study clean interfaces samples must be kept cold at all stages
- Similarities in  $T_C$ ,  $H_{C2}$  and x-ray crystallography identifies  $\text{NiBi}_3$  as the origin of the superconductivity after forming by annealing
- A large effective superconducting thickness and the expected thin  $\text{NiBi}_3$  layer indicate proximity effect in the bismuth layer
- Even with  $\text{NiBi}_3$  at the interface the results here and elsewhere show that it is unlikely to be a typical type-II superconductor

## References

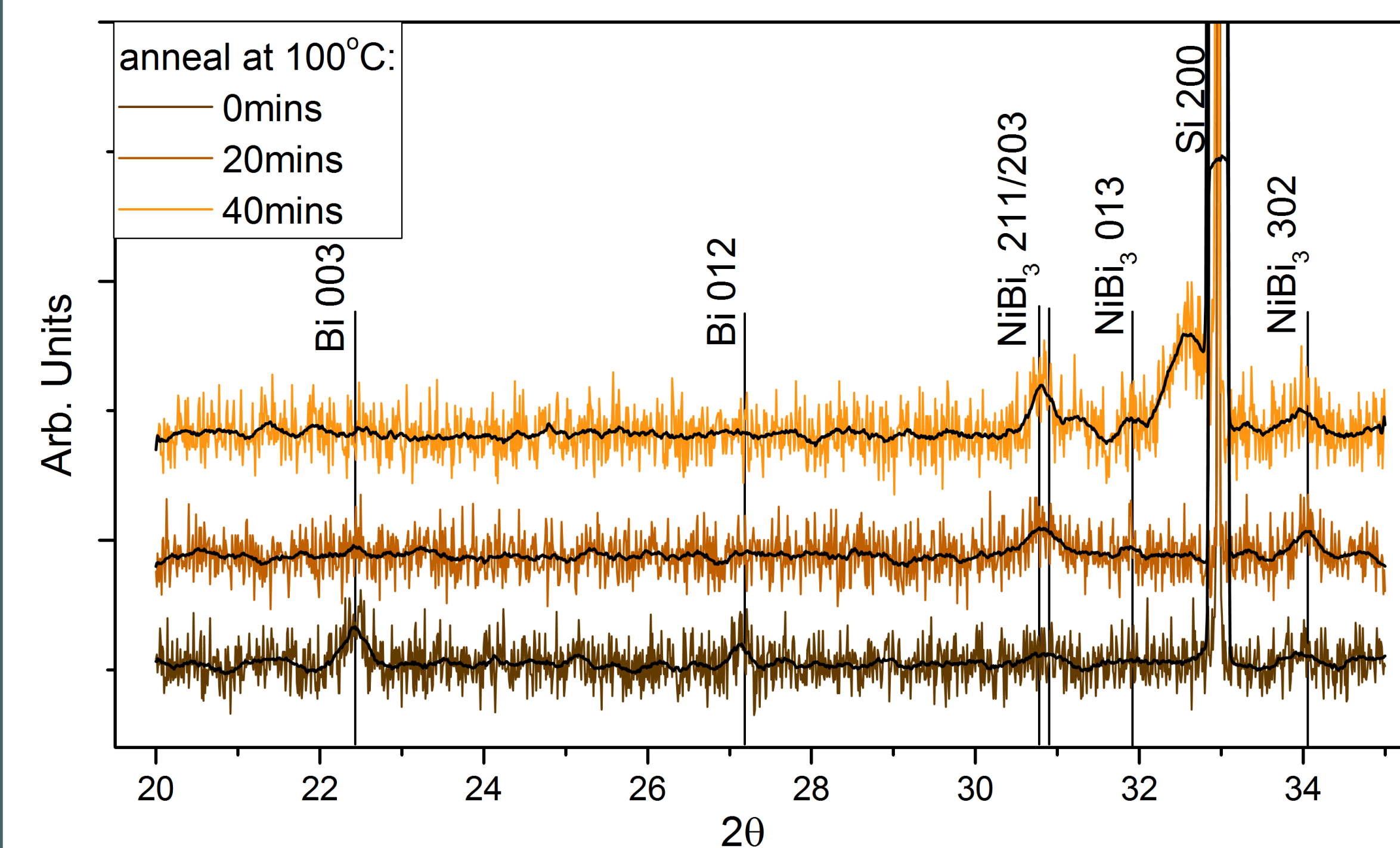
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## Sample Growth and Annealing

- Samples were grown by DC magnetron sputtering at  $20^\circ\text{C}$  and a base pressure of  $9 \times 10^{-8}$  torr, afterward they were stored at  $\approx 4^\circ\text{C}$  to prevent annealing
- Superconducting  $T_C$  was maximized for 50 nm of bismuth and 6 nm of nickel, 5 nm tantalum cap to prevent oxidization. Superconductivity known to be independent on growth order
- Annealing was done using a preheated hot plate with a cover for uniformity, this rapidly heated and cooled the low thermal mass samples placed on it, reducing timing uncertainty

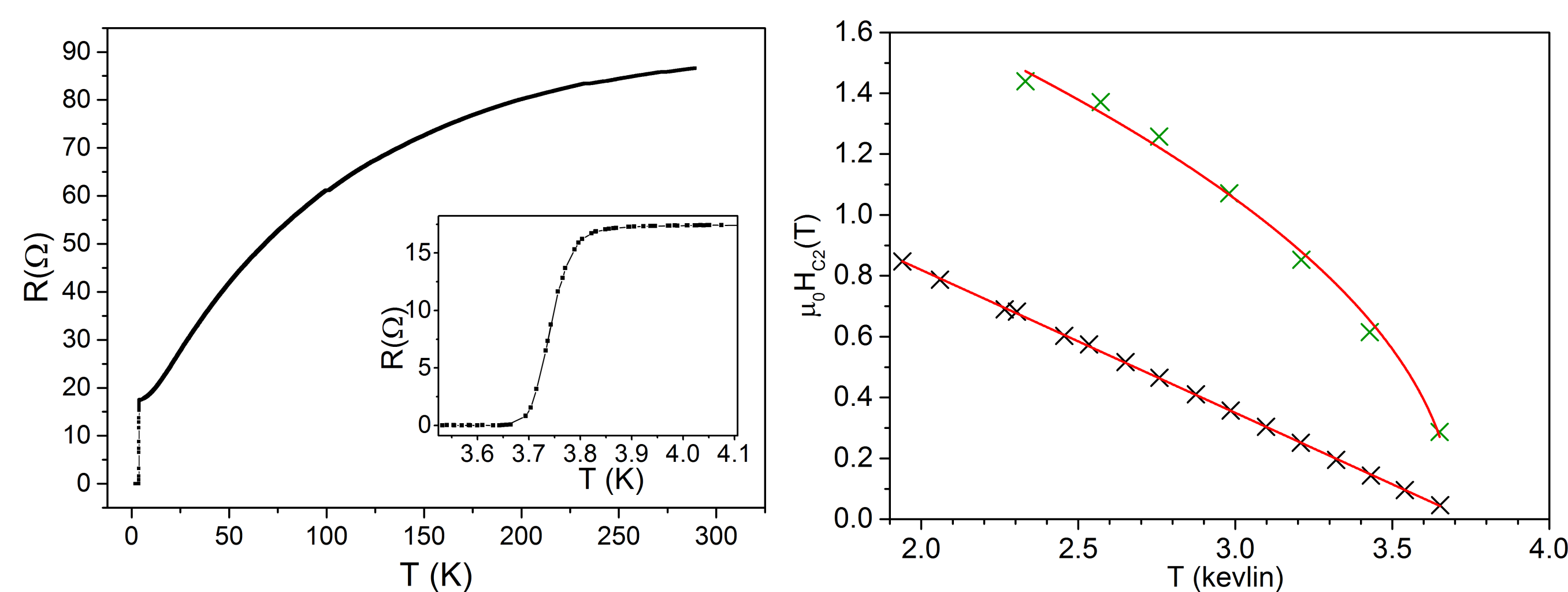


- Clear aging of the sample at  $\approx 21^\circ\text{C}$  as the onset point of the meissner effect increased over a period of 2 weeks, magnetization is measured as an absolute value, sample unchanged at  $\approx 4^\circ\text{C}$
- The annealing rate against temperature was fitted well by the Arrhenius equation for a thermally activated reaction with an associated activation energy of  $(0.86 \pm 0.06)$  eV
- The low activation energy is similar to bismuth gold interface diffusion with activation energies of  $\approx 1$  eV [5] and the low melting point of bismuth ( $271^\circ\text{C}$ ) explains why bismuth is so mobile and can diffuse across the interface at low temperatures



- Annealed samples showed  $\text{NiBi}_3$  peaks in high angle x-ray diffraction along with the Si 200 forbidden peak
- The timescale of the appearance of these peaks was of similar timescale to the meissner onset rate which took 30 mins to saturate the  $T_C$  at  $100^\circ\text{C}$
- Shoulder on the Si 200 for 40 mins annealed is substrate related and not part of the thin film

## Superconductivity and Magnetic Properties



- 4-point measurements of a samples annealed at  $150^\circ\text{C}$  until the superconducting  $T_C$  has saturated at 3.8 k, bulk  $\text{NiBi}_3$   $T_C$  is 4.1 k
- $H_{C2}$  temperature dependence is fitted well by the GL model for a thin superconductor with an effective superconducting thickness of 37 nm and a coherence length of 15 nm

- Since the  $\text{NiBi}_3$  layer is expected to be very thin it must be proximitizing the remaining bismuth layer which is known to preserve superconductivity up to 125 nm
- Above  $H_{C2}$  exists a ferromagnetic like magnetization, the above  $T_C$  hysteresis loop (Red) has a similar saturation moment
- The coexistence of superconductivity and ferromagnetism is unusual, although it has been suggested that  $\text{NiBi}_3$  is also simultaneously superconducting and ferromagnetic [6]

